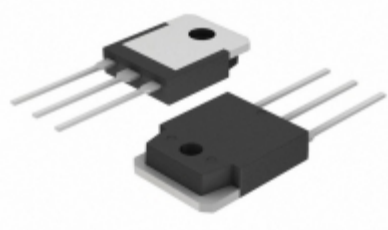



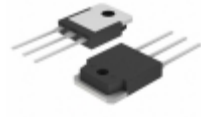
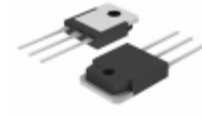


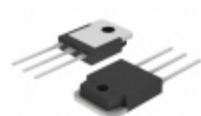


	FQA8N80C	
	Hersteller-Teilenummer:	FQA8N80C
	Hersteller / Marke:	AMI Semiconductor / ON Semiconductor
	Teil der Beschreibung:	MOSFET N-CH 800V 8.4A TO-3P
	Datenblätter:	 FQA8N80C.pdf
	RoHs Status:	Bleifrei / RoHS-konform
<p>Image may be representation. See specs for product details.</p>	Lagerzustand:	New original, 1550 pcs Stock Available.
	Liefern von:	Hong Kong
	Versandweg:	DHL/Fedex/TNT/UPS/EMS

Spezifikationen

Teilenummer	FQA8N80C
Hersteller	AMI Semiconductor / ON Semiconductor
Beschreibung	MOSFET N-CH 800V 8.4A TO-3P
Kategorie	Diskrete Halbleiterprodukte > Transistoren-FETs ,
Teilstatus	1550 pcs Stock
detaillierte Beschreibung	N-Channel 800V 8.4A (Tc) 220W (Tc) Through Hole
Serie	QFET®
Technologie	MOSFET (Metal Oxide)
Betriebstemperatur	-55°C ~ 150°C (TJ)
Befestigungsart	Through Hole
Verpackung / Gehäuse	TO-3P-3, SC-65-3
Supplier Device-Gehäuse	TO-3PN
Verlustleistung (max)	220W (Tc)
Typ FET	N-Channel
FET-Merkmal	-
Drain-Source-Spannung (Vdss)	800V
Strom - Ununterbrochener Abfluss (Id) bei 25 ° C	8.4A (Tc)
Rds On (Max) @ Id, Vgs	1.55 Ohm @ 4.2A, 10V
VGS (th) (Max) @ Id	5V @ 250µA
Gate Charge (Qg) (Max) @ Vgs	45nC @ 10V
Eingabekapazität (Ciss) (Max) @ Vds	2050pF @ 25V
Antriebsspannung (Max Rds On, Min Rds On)	10V
Vgs (Max)	±30V
Verpackung	Tube
Bleifreier Status / RoHS-Status	Lead free / RoHS Compliant
Feuchtigkeitsempfindlichkeitsniveau (MSL)	1 (Unlimited)


















FQA8N80C ist neu im Original, Suche FQA8N80C Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie FQA8N80C AMI Semiconductor / ON Semiconductor mit Garantie und Vertrauen. Anfrage FQA8N80C: Info@Y-IC.com

Sie können auch interessiert sein:

 FQA8N90C Fairchild/ON Semiconductor MOSFET N-CH 900V 8A TO-3P	 FQA8N80C_F109 AMI Semiconductor / ON Semiconductor MOSFET N-CH 800V 8.4A TO-3P	 FQA8N100C AMI Semiconductor / ON Semiconductor MOSFET N-CH 1000V 8A TO-3P	 FQA8N80C Fairchild/ON Semiconductor MOSFET N-CH 800V 8.4A TO-3P
 FQA8N100C Fairchild/ON Semiconductor MOSFET N-CH 1000V 8A TO-3P	 FQA8N90C AMI Semiconductor / ON Semiconductor MOSFET N-CH 900V 8A TO-3P	 FQA8N80 Original FQA8N80 Original	 FQA85N06 AMI Semiconductor / ON Semiconductor MOSFET N-CH 60V 100A TO-3P

heiße Teile

Mehr

 FQA46P06	 FQA46P15	 FQA47P06	 D FQA47P06	 FQA48N20
 FQA48N20	 FQA55N10	 D FQA55N10	 FQA55N25	 FQA55N25
 FQA62N25C	 FQA62N25C	 FQA65N06	 FQA65N06	 FQA65N20
 D FQA65N20	 FQA6N90C	 FQA70N10	 FQA70N10	 FQA70N15
 FQA70N15	 FQA7N80C	 FQA7N80C	 FQA8N100C	 FQA8N100C
 FQA8N80C	 FQA90N08	 D FQA90N08	 FQA90N10V2	 FQA90N10V2
 FQA90N15	 D FQA90N15	 FQA90N15_F109	 FQA9N90C	 FQA9N90C
 FQA9N90C_F109	 FQA9N90_F109	 FQA9F10N80	 FQA9F10N80	 FQA9F11N40
 FQA9F11N40	 FQA9F11N90	 FQA9F11N90	 D FQA9F11N90C	 FQA9F11N90C
 FQA9F12P20	 FQA9F12P20	 FQA9F13N50	 FQA9F13N80	 FQA9F13N80

Contact us: Info@Y-IC.com

HINZUFÜGEN: Einheit A5-B5 Nr.509, 5 / F Sing Win Fabrikgebäude, 15-17 Shing Yip St, Kwun Tong, Kowloon, HongKong.

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